

Z0103NA0

4Q Triac

Rev. 02 — 21 March 2011

Product data sheet

1. Product profile

1.1 General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

1.3 Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ °C}$; $t_{\text{p}} = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	-	12.5	A
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 45\text{ °C}$; see Figure 1 ; see Figure 3 ; see Figure 2	-	-	1	A

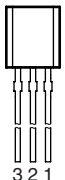
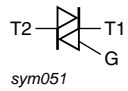


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G+;$ $T_j = 25\text{ }^\circ\text{C};$ see Figure 7	0.2	-	5	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		 sym051
2	G	gate		
3	T1	main terminal 1		

SOT54 (TO-92)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0103NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 45\text{ }^{\circ}\text{C}$; see Figure 1 ; see Figure 3 ; see Figure 2	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; see Figure 4 ; see Figure 5	-	12.5	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 16.7\text{ ms}$	-	13.8	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	0.78	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 1\text{ A}$; $I_G = 20\text{ mA}$; $dI_G/dt = 100\text{ mA}/\mu\text{s}$; T2+ G+	-	50	$\text{A}/\mu\text{s}$
		$I_T = 1\text{ A}$; $I_G = 20\text{ mA}$; $dI_G/dt = 100\text{ mA}/\mu\text{s}$; T2+ G-	-	50	$\text{A}/\mu\text{s}$
		$I_T = 1\text{ A}$; $I_G = 20\text{ mA}$; $dI_G/dt = 100\text{ mA}/\mu\text{s}$; T2- G-	-	50	$\text{A}/\mu\text{s}$
		$I_T = 1\text{ A}$; $I_G = 20\text{ mA}$; $dI_G/dt = 100\text{ mA}/\mu\text{s}$; T2- G+	-	20	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$

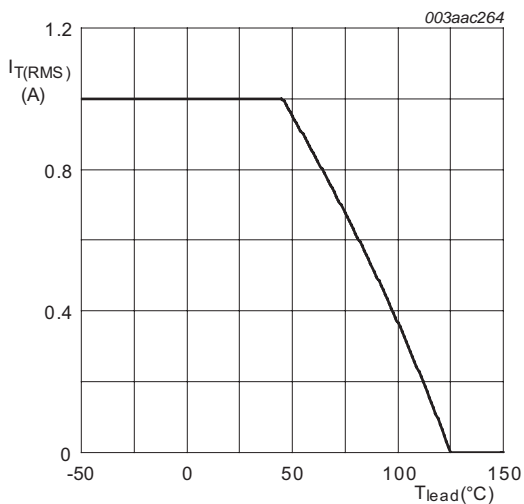
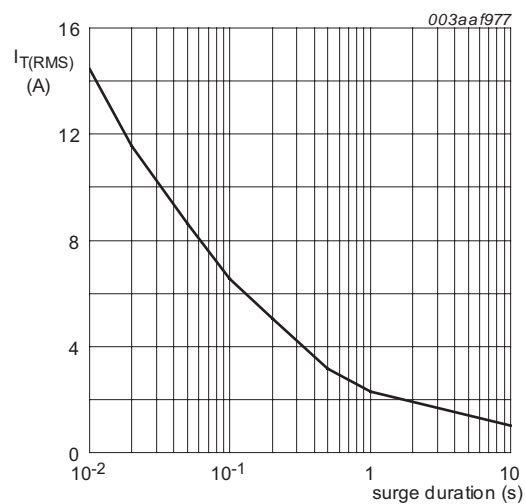


Fig 1. RMS on-state current as a function of lead temperature; maximum values



$$f = 50\text{ Hz}, T_{lead} = 45\text{ }^{\circ}\text{C}$$

Fig 2. RMS on-state current as a function of surge duration; maximum values

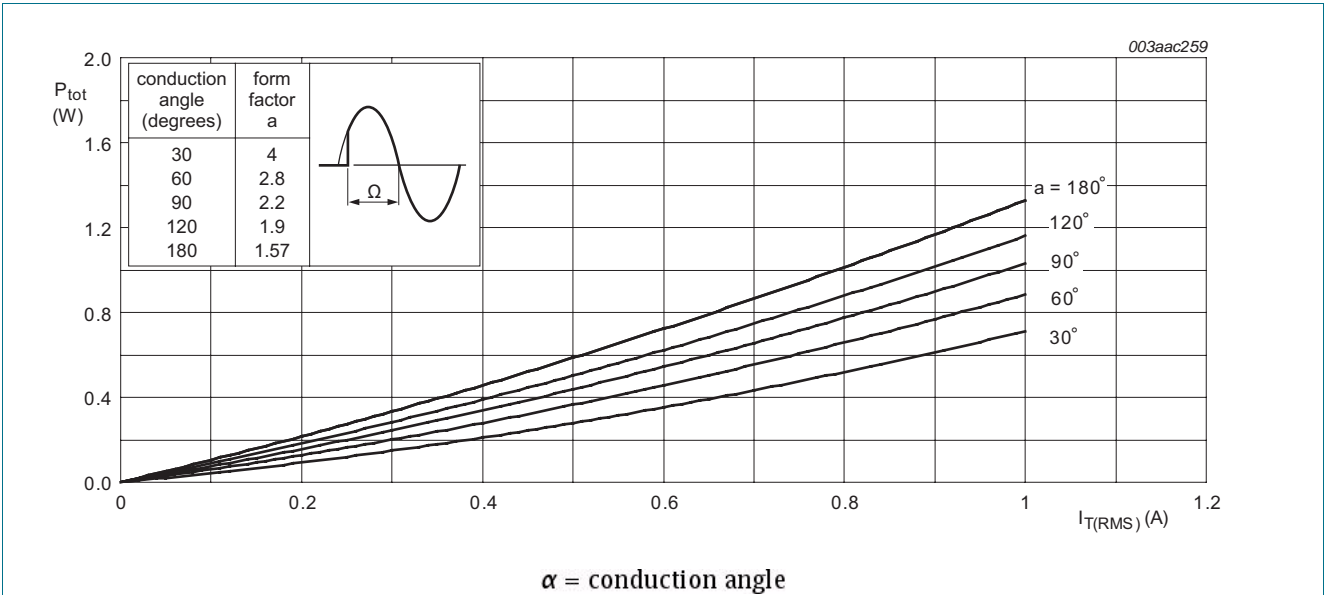


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

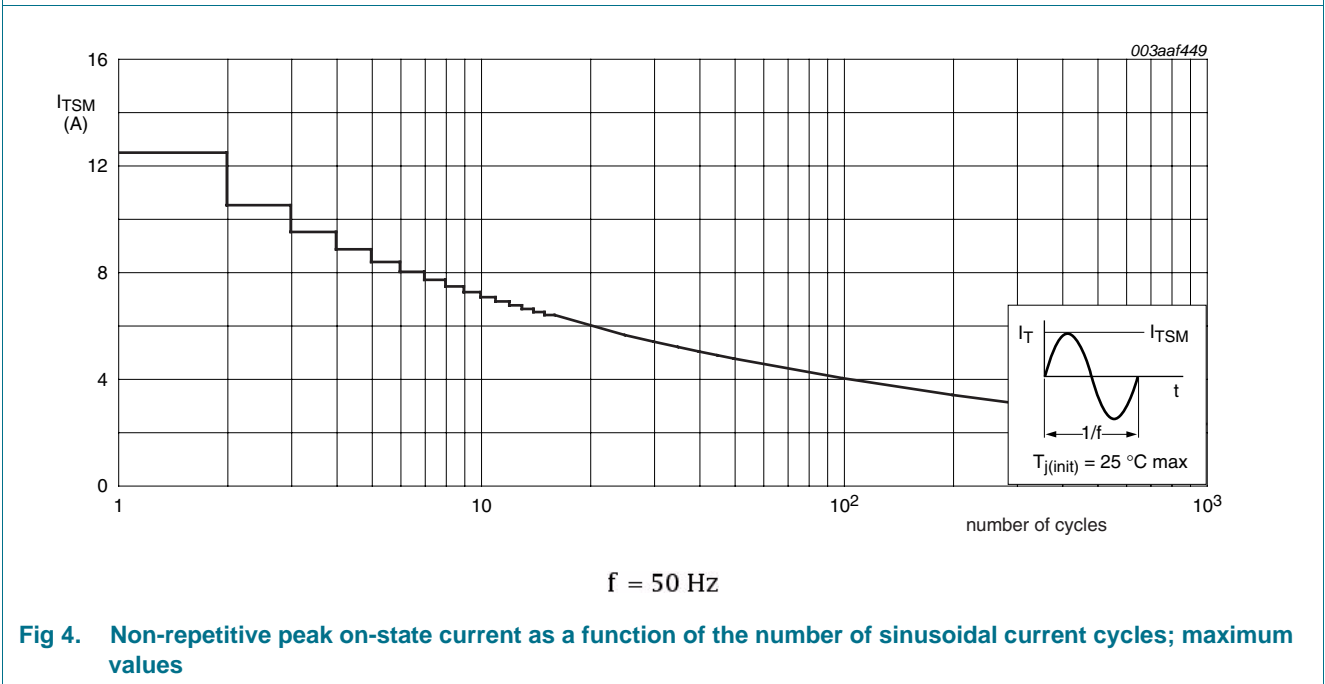
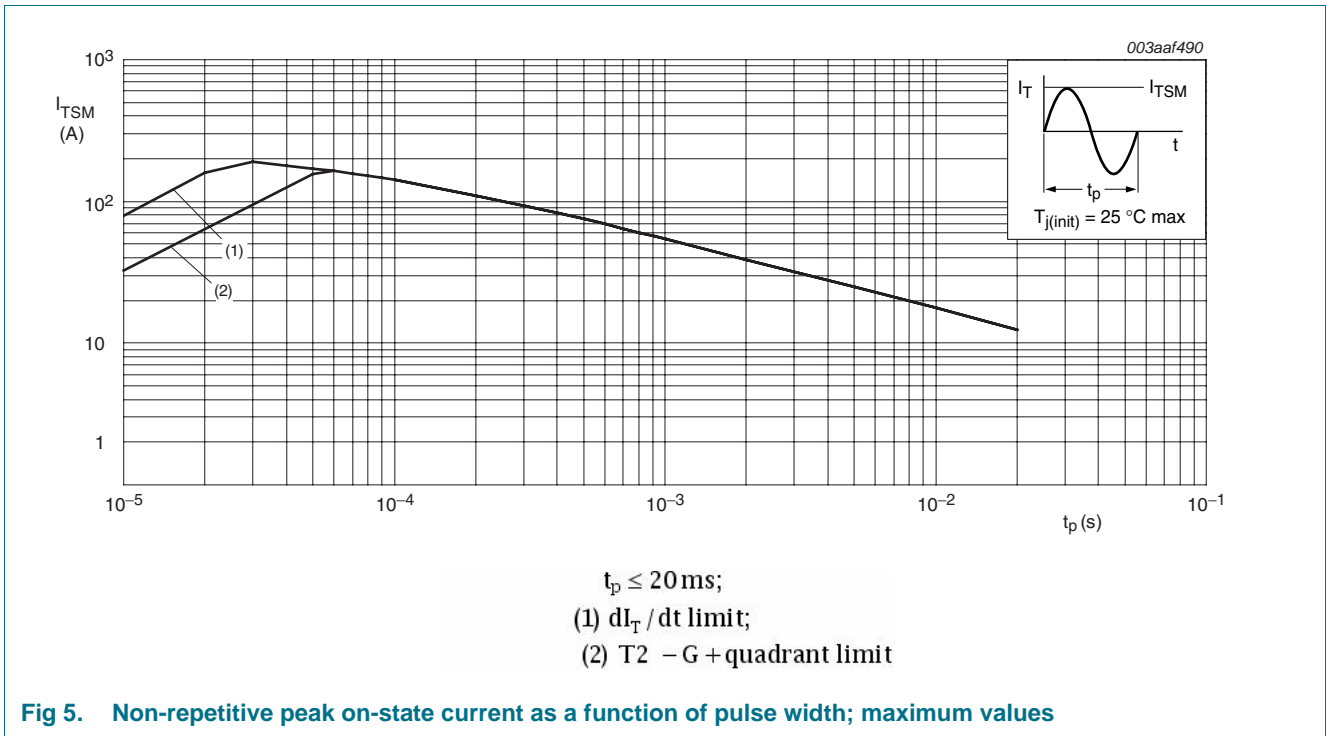


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; printed circuit board mounted; lead length 4 mm	-	150	-	K/W

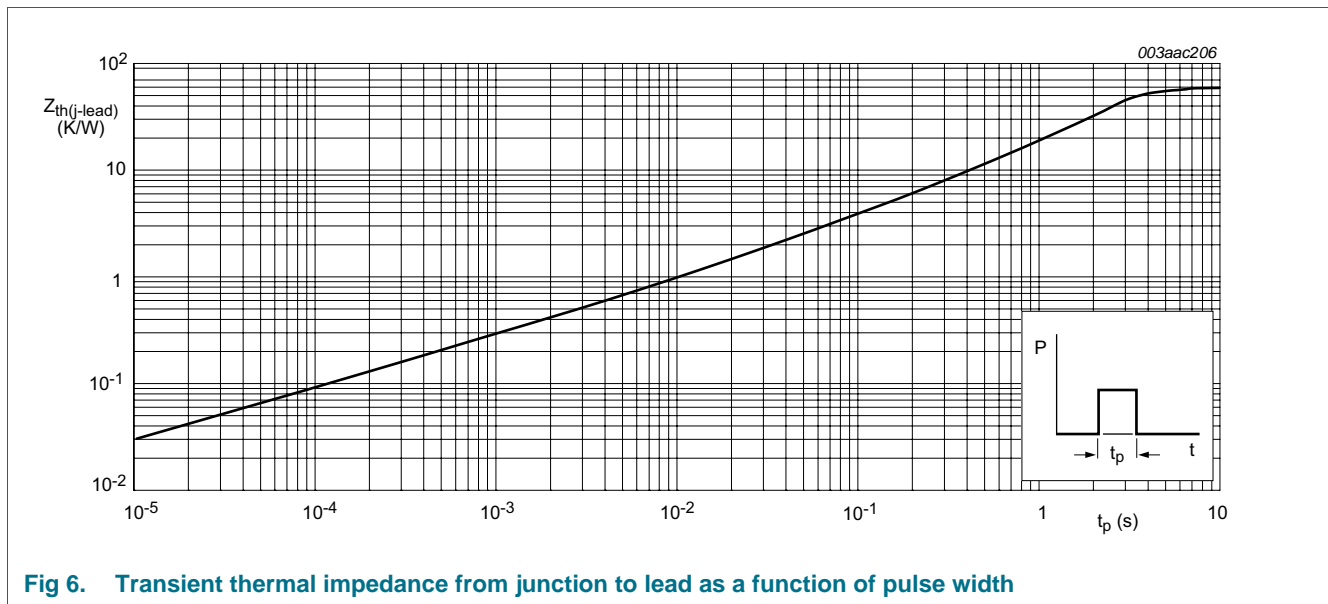
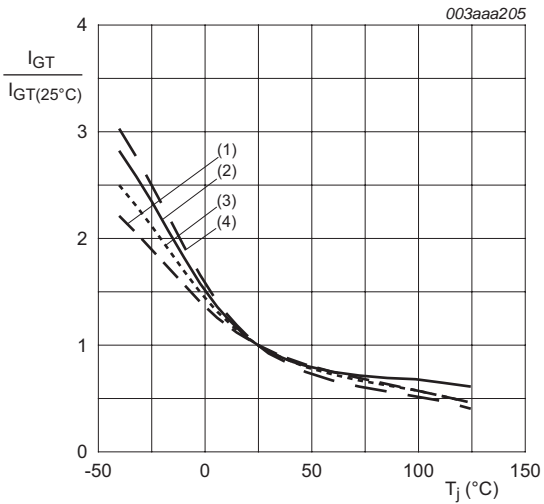


Fig 6. Transient thermal impedance from junction to lead as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 7	0.2	-	3	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; see Figure 7	0.2	-	5	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	7	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	20	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; see Figure 8	-	-	7	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ °C}$; see Figure 8	-	-	7	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; see Figure 9	-	-	7	mA
V_T	on-state voltage	$I_T = 1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 10	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ °C}$; see Figure 11	-	-	1.3	V
		$V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ °C}$; see Figure 11	0.2	-	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 125\text{ °C}$	-	-	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 110\text{ °C}$; gate open circuit; exponential waveform; see Figure 12	80	-	-	V/ μ s
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 110\text{ °C}$; $dI_{com}/dt = 0.44\text{ A/ms}$; gate open circuit	0.5	-	-	V/ μ s



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger current as a function of junction temperature

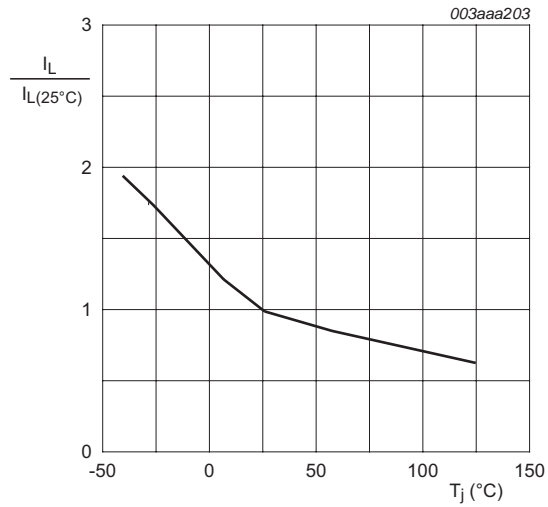


Fig 8. Normalized latching current as a function of junction temperature

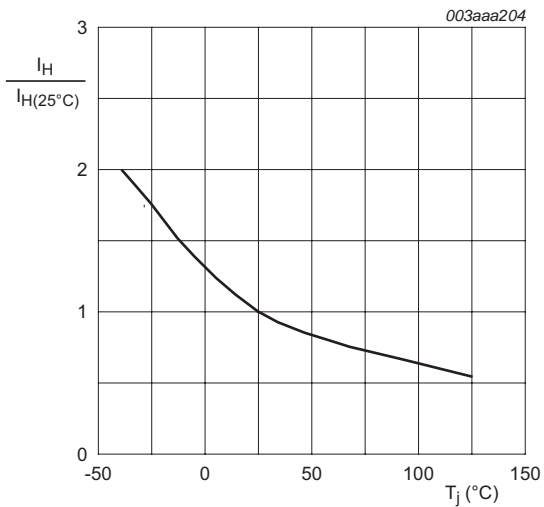
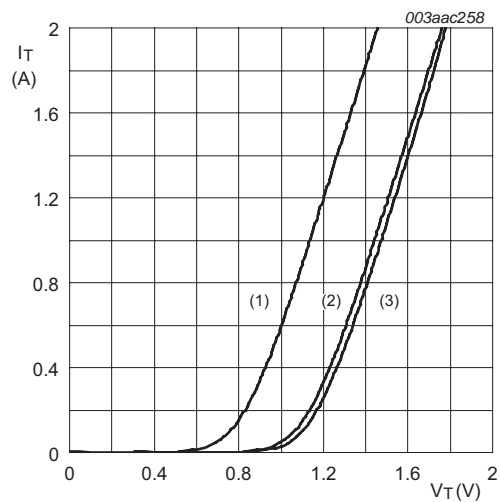


Fig 9. Normalized holding current as a function of junction temperature



$V_o = 1.13 \text{ V}$

$R_s = 0.31 \text{ } \Omega$

(1) $T_j = 125 \text{ } ^\circ\text{C}$; typical values

(2) $T_j = 125 \text{ } ^\circ\text{C}$; maximum values

(3) $T_j = 25 \text{ } ^\circ\text{C}$; maximum values

Fig 10. On-state current as a function of on-state voltage

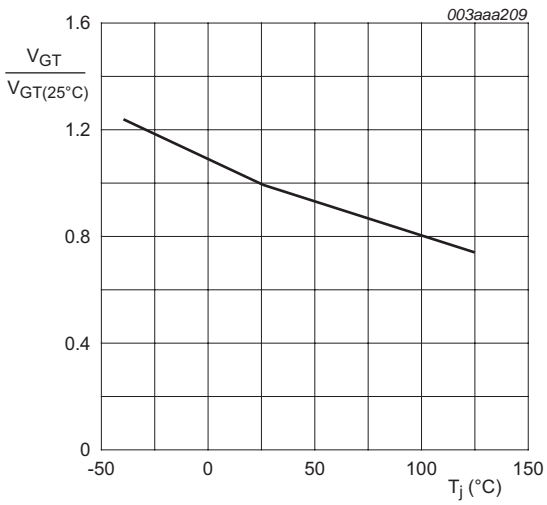
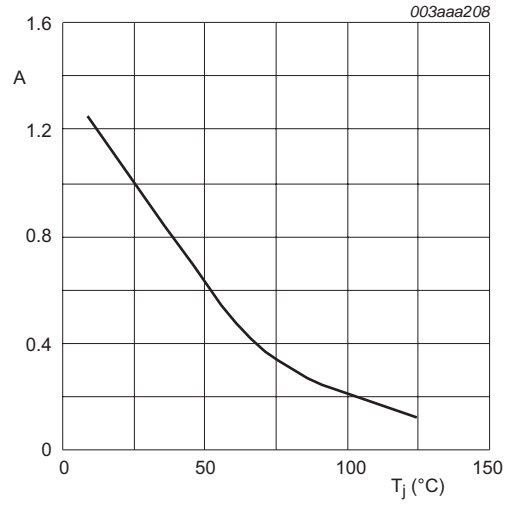


Fig 11. Normalized gate trigger voltage as a function of junction temperature



$$A = \frac{dV_D / dt}{dV_{D(25^\circ C)} / dt}$$

Fig 12. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

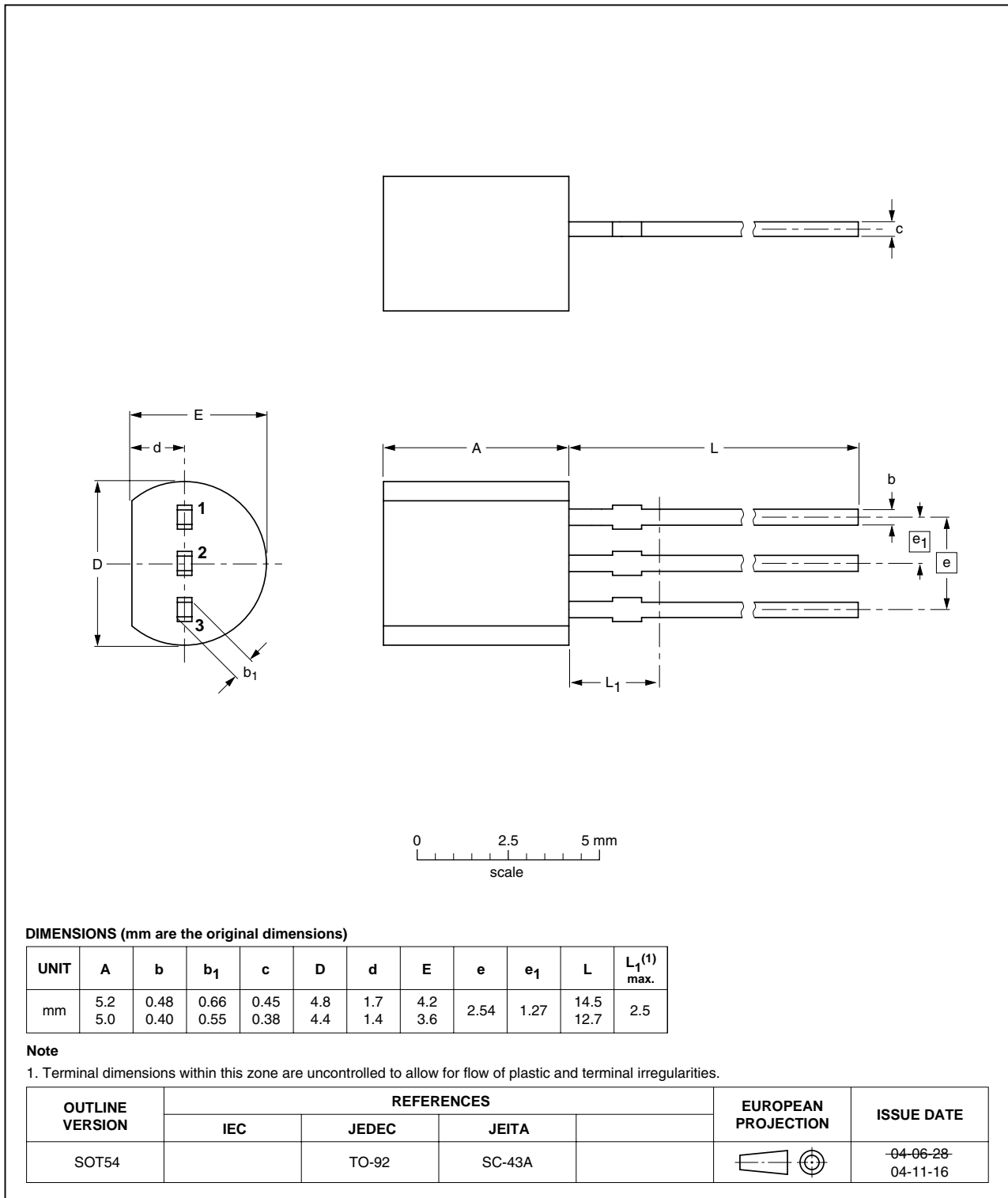


Fig 13. Package outline SOT54 (TO-92)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0103NA0 v.2	20110321	Product data sheet	-	Z0103NA0 v.1
Modifications:	• Various changes to content.			
Z0103NA0 v.1	20110103	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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